

# Dual NPN Bias Resistor Transistors R1 = 100 k $\Omega$ , R2 = 100 k $\Omega$

NPN Transistors with Monolithic Bias Resistor Network

# MUN5236DW1, NSBC115EDXV6

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base-emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

## **MAXIMUM RATINGS**

(T<sub>A</sub> = 25 °C, common for Q<sub>1</sub> and Q<sub>2</sub>, unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector-Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current - Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	40	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

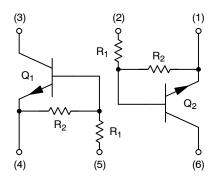
#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
MUN5236DW1T1G	SOT-363	3,000/Tape & Reel
NSBC115EDXV6T1G	SOT-563	4,000/Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

1

#### **PIN CONNECTION**



## **MARKING DIAGRAM**



SOT-363 CASE 419B





SOT-563 CASE 463A



7N = Specific Device Code

M = Date Code\*
■ Pb-Free Package

(Note: Microdot may be in either location)

<sup>\*</sup>Date Code orientation may vary depending upon manufacturing location.

# THERMAL CHARACTERISTICS

Characteristic			Max	Unit
MUN5236DW1 (SOT-363) ONE JUNCTION HEATED				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	187 256 1.5 2.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	670 490	°C/W
MUN5236DW1 (SOT-363) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation $T_{A} = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1) (Note 2)	P <sub>D</sub>	250 385 2.0 3.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	493 325	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ hetaJL}$	188 208	°C/W
Junction and Storage Temperature Range		$T_J$ , $T_{stg}$	-55 to +150	°C
NSBC115EDXV6 (SOT-563) ONE JUNCTION HEATED				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 1)	$P_{D}$	357 2.9	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	350	°C/W
NSBC115EDXV6 (SOT-563) BOTH JUNCTION HEATED (Note 3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 1)	P <sub>D</sub>	500 4.0	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1)	$R_{ hetaJA}$	250	°C/W
Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

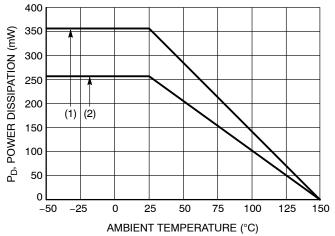
FR-4 @ Minimum Pad.
 FR-4 @ 1.0 x 1.0 Inch Pad.
 Both junction heated values assume total power is sum of two equally powered channels.

**ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, common for Q<sub>1</sub> and Q<sub>2</sub>, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					•
Collector-Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	-	100	nAdc
Collector-Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	-	-	500	nAdc
Emitter-Base Cutoff Current $(V_{EB} = 6.0 \text{ V}, I_C = 0)$	I <sub>EBO</sub>	-	-	0.05	mAdc
Collector-Base Breakdown Voltage ( $I_C = 10 \mu A$ , $I_E = 0$ )	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Collector-Emitter Breakdown Voltage (Note 4) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	50	-	-	Vdc
ON CHARACTERISTICS					
DC Current Gain (Note 4) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	80	150	-	
Collector-Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0.3 mA)	V <sub>CE(sat)</sub>	-	-	0.25	V
Input Voltage (Off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	-	1.2	0.5	Vdc
Input Voltage (On) (V <sub>CE</sub> = 0.3 V, I <sub>C</sub> = 1.0 mA)	V <sub>i(on)</sub>	3.0	1.7	-	Vdc
Output Voltage (On) ( $V_{CC}$ = 5.0 V, $V_{B}$ = 5.5 V, $R_{L}$ = 1.0 k $\Omega$ )	V <sub>OL</sub>	-	-	0.2	Vdc
Output Voltage (Off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.25 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	70	100	130	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

<sup>4.</sup> Pulsed Condition: Pulse Width = 300 ms, Duty Cycle ≤ 2%.



- (1) SOT-363;  $1.0 \times 1.0$  Inch Pad
- (2) SOT-563; Minimum Pad

Figure 1. Derating Curve

# TYPICAL CHARACTERISTICS MUN5236DW1, NSBC115EDXV6

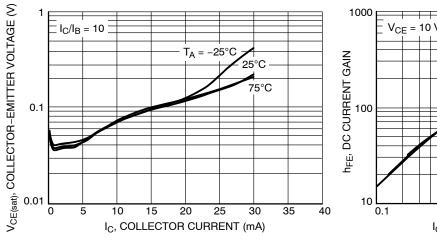
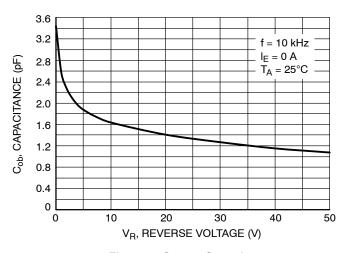


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain



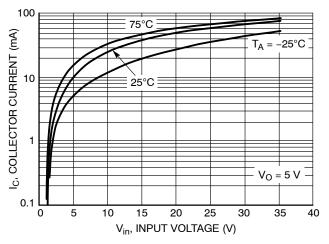


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

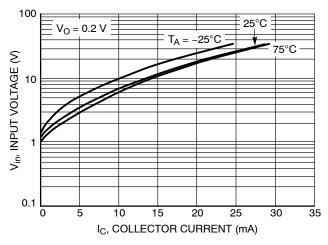


Figure 6. Input Voltage vs. Output Current

# **REVISION HISTORY**

Revision	Description of Changes	Date
2	Rebranded the Data Sheet to onsemi format	5/28/2025





E1

e

В

## SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 **ISSUE Z**

**DATE 18 APR 2024** 

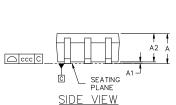
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20
- DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
  DATUMS A AND B ARE DETERMINED AT DATUM H.
- DIMENSIONS 6 AND C APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP. 6.
- DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION 6 AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

aaa

bbb

ccc ddd

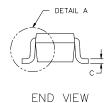


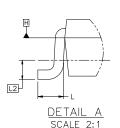
TOP VIEW

∆aaa H A−B

<u></u> БЬБ С

⊕ ddd M C A−B D





DIM	MIN.	NOM.	MAX.
А			1.10
A1	0.00		0.10
A2	0.70	0.90	1.00
b	0.15	0.20	0.25
С	0.08	0.15	0.22
D	2.00 BSC		
E	2.10 BSC		
E1	1.25 BSC		
е	0.65 BSC		
L	0.26	0.36	0.46
L2	0.15 BSC		

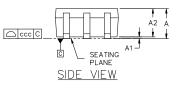
0.15

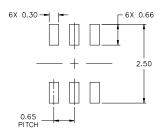
0.30

0.10

0.10

MILLIMETERS





## RECOMMENDED MOUNTING FOOTPRINT\*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

# **GENERIC MARKING DIAGRAM\***



XXX = Specific Device Code

= Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)

- \*Date Code orientation and/or position may vary depending upon manufacturing location.
- \*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

# **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42985B Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLE!"		
DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P		PAGE 1 OF 2

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# SC-88 2.00x1.25x0.90, 0.65P CASE 419B-02 ISSUE Z

**DATE 18 APR 2024** 

STYLE 1: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 2: CANCELLED	STYLE 3: CANCELLED	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. COLLECTOR 4. EMITTER 5. BASE 6. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 6: PIN 1. ANODE 2 2. N/C 3. CATHODE 1 4. ANODE 1 5. N/C 6. CATHODE 2
STYLE 7: PIN 1. SOURCE 2 2. DRAIN 2 3. GATE 1 4. SOURCE 1 5. DRAIN 1 6. GATE 2	STYLE 8: CANCELLED	STYLE 9: PIN 1. EMITTER 2 2. EMITTER 1 3. COLLECTOR 1 4. BASE 1 5. BASE 2 6. COLLECTOR 2	STYLE 10: PIN 1. SOURCE 2 2. SOURCE 1 3. GATE 1 4. DRAIN 1 5. DRAIN 2 6. GATE 2	STYLE 11: PIN 1. CATHODE 2 2. CATHODE 2 3. ANODE 1 4. CATHODE 1 5. CATHODE 1 6. ANODE 2	STYLE 12: PIN 1. ANODE 2 2. ANODE 2 3. CATHODE 1 4. ANODE 1 5. ANODE 1 6. CATHODE 2
STYLE 13: PIN 1. ANODE 2. N/C 3. COLLECTOR 4. EMITTER 5. BASE 6. CATHODE	STYLE 14: PIN 1. VREF 2. GND 3. GND 4. IOUT 5. VEN 6. VCC	STYLE 15: PIN 1. ANODE 1 2. ANODE 2 3. ANODE 3 4. CATHODE 3 5. CATHODE 2 6. CATHODE 1	STYLE 16: PIN 1. BASE 1 2. EMITTER 2 3. COLLECTOR 2 4. BASE 2 5. EMITTER 1 6. COLLECTOR 1	STYLE 17: PIN 1. BASE 1 2. EMITTER 1 3. COLLECTOR 2 4. BASE 2 5. EMITTER 2 6. COLLECTOR 1	STYLE 18: PIN 1. VIN1 2. VCC 3. VOUT2 4. VIN2 5. GND 6. VOUT1
STYLE 19: PIN 1. I OUT 2. GND 3. GND 4. V CC 5. V EN 6. V REF	STYLE 20: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR	STYLE 21: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. N/C 6. CATHODE 1	STYLE 22: PIN 1. D1 (i) 2. GND 3. D2 (i) 4. D2 (c) 5. VBUS 6. D1 (c)	STYLE 23: PIN 1. Vn 2. CH1 3. Vp 4. N/C 5. CH2 6. N/C	STYLE 24: PIN 1. CATHODE 2. ANODE 3. CATHODE 4. CATHODE 5. CATHODE 6. CATHODE
STYLE 25: PIN 1. BASE 1 2. CATHODE 3. COLLECTOR 2 4. BASE 2 5. EMITTER 6. COLLECTOR 1	STYLE 26: PIN 1. SOURCE 1 2. GATE 1 3. DRAIN 2 4. SOURCE 2 5. GATE 2 6. DRAIN 1	STYLE 27: PIN 1. BASE 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. EMITTER 2 6. COLLECTOR 2	STYLE 28: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 29: PIN 1. ANODE 2. ANODE 3. COLLECTOR 4. EMITTER 5. BASE/ANODE 6. CATHODE	STYLE 30: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1

Note: Please refer to datasheet for style callout. If style type is not called out in the datasheet refer to the device datasheet pinout or pin assignment.

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DESCRIPTION:	SC-88 2.00x1.25x0.90, 0.65P		PAGE 2 OF 2

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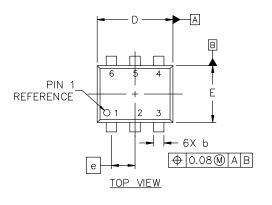


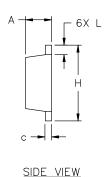
## SOT-563-6 1.60x1.20x0.55, 0.50P CASE 463A **ISSUE J**

**DATE 15 FEB 2024** 

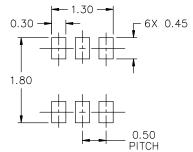
#### NOTES:

- 1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.





MIG	MILLIMETERS			
ויונע	MIN.	N□M.	MAX.	
Α	0.50	0.55	0.60	
b	0.17	0.22	0.27	
	0.08	0.13	0.18	
D	1,50	1.60	1.70	
E	1.10	1,20	1.30	
е	0.50 BSC			
Н	1.50	1.60	1.70	
Ĺ	0.10	0.20	0.30	



STYLE 1: PIN 1. EMITTER 1 2. BASE 1 3. COLLECTOR 2 4. EMITTER 2 5. BASE 2 6. COLLECTOR 1	STYLE 2: PIN 1. EMITTER 1 2. EMITTER 2 3. BASE 2 4. COLLECTOR 2 5. BASE 1 6. COLLECTOR 1	STYLE 3: PIN 1. CATHODE 1 2. CATHODE 1 3. ANODE/ANODE 2 4. CATHODE 2 5. CATHODE 2 6. ANODE/ANODE 1
6. COLLECTOR 1	6. COLLECTOR 1	6. ANDDE/ANDDE 1

STYLE 6: PIN 1. CATHODE 2. ANODE

CATHODE

4. CATHODE 5. CATHODE

6. CATHODE

RECOMMENDED	MOUNTING	FOOTPRINT*

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98AON11126D

3. ANDDE

4. ANDDE 5. CATHODE

6. CATHODE

STYLE 5: PIN 1. CATHODE 2. CATHODE

# **GENERIC** MARKING DIAGRAM\*



XX = Specific Device Code M = Month Code = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 10:	STYLE 11:
PIN 1. CATHODE 1	PIN 1. EMITTER 2
2. N/C	2. BASE 2
3. CATHODE 2	3. COLLECTOR 1
4. ANODE 2	4. EMITTER 1
5. N/C	5. BASE 1
6. AN□DE 1	6. COLLECTOR 2

STYLE 4: PIN 1. COLLECTOR 2. COLLECTOR

3. BASE

4. EMITTER
5. COLLECTOR
6. COLLECTOR

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